PROCEEDINGS OF SPIE

Advances in Patterning Materials and Processes XXXVII

Roel Gronheid
Daniel P. Sanders
Editors

24–26 February 2020
San Jose, California, United States

Sponsored and Published by
SPIE

Volume 11326

Proceedings of SPIE 0277-786X, V. 11326

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

Advances in Patterning Materials and Processes XXXVII, edited by Roel Gronheid, Daniel P. Sanders, Proc. of SPIE Vol. 11326, 1132601 · © 2020 SPIE · CCC code: 0277-786X/20/$21 · doi: 10.1117/12.2571086

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Please use the following format to cite material from these proceedings:
Author(s), "Title of Paper," in *Advances in Patterning Materials and Processes XXXVII*, edited by Roel Gronheid, Daniel P. Sanders, Proceedings of SPIE Vol. 11326 (SPIE, Bellingham, WA, 2020) Seven-digit Article CID Number.

ISSN: 0277-786X
ISSN: 1996-756X (electronic)

ISBN: 9781510634190
ISBN: 9781510634206 (electronic)

Published by
SPIE
P.O. Box 10, Bellingham, Washington 98227-0010 USA
Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445
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